

● General Description

The AGM30P110D combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$

This device is ideal for load switch and battery protection applications.

● Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

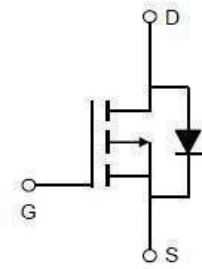
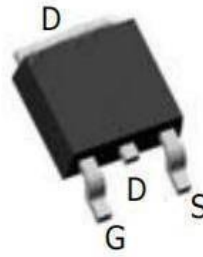
● Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

Product Summary

BVDSS	RDS(ON)	ID
-30V	2.9mΩ	-138A

TO-252 Pin Configuration



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM30P110D	AGM30P110D	TO-252	----	----	2500

Table 1. Absolute Maximum Ratings (TA=25°C)

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	-30	V
VGS	Gate-Source Voltage (VDS=0V)	±20	V
ID	Drain Current-Continuous(Tc=25°C) (Note 1)	-138	A
	Drain Current-Continuous(Tc=100°C)	-98	A
IDM (pluse)	Drain Current-Continuous@ Current-Pulsed (Note 2)	-550	A
PD	Maximum Power Dissipation(Tc=25°C)	138	w
	Maximum Power Dissipation(Tc=100°C)	55.5	w
EAS	Avalanche energy (Note 3)	--	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State) ¹	---	62	°C/W
RθJC	Thermal Resistance Junction-Case ¹	---	0.9	°C/W

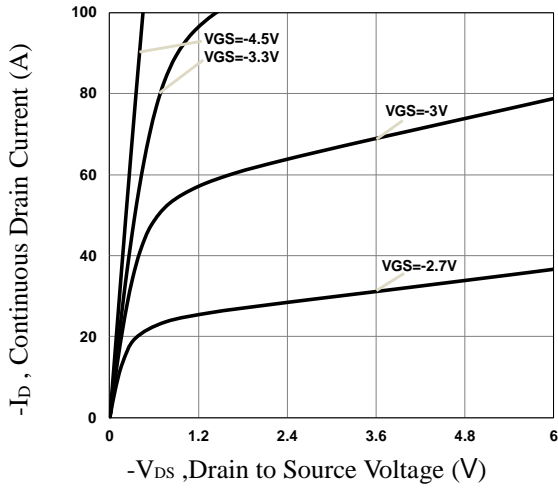
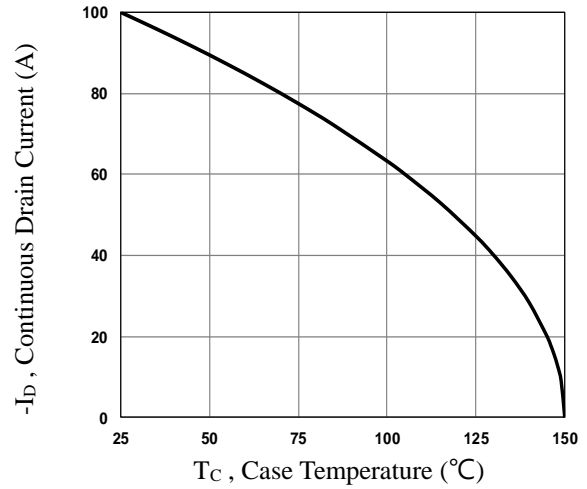
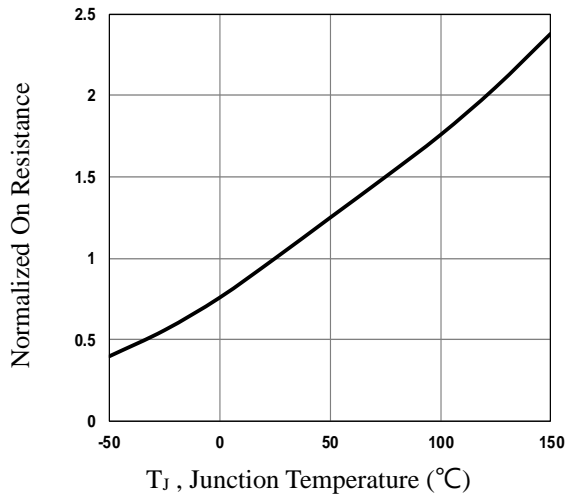
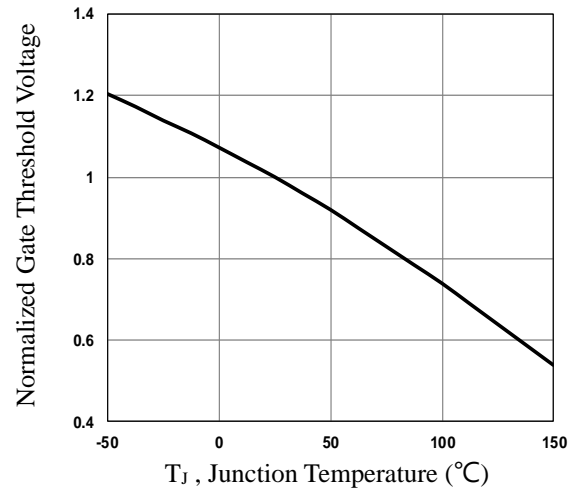
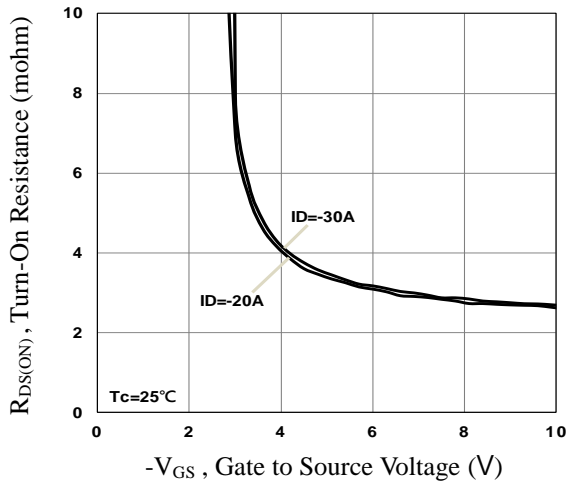
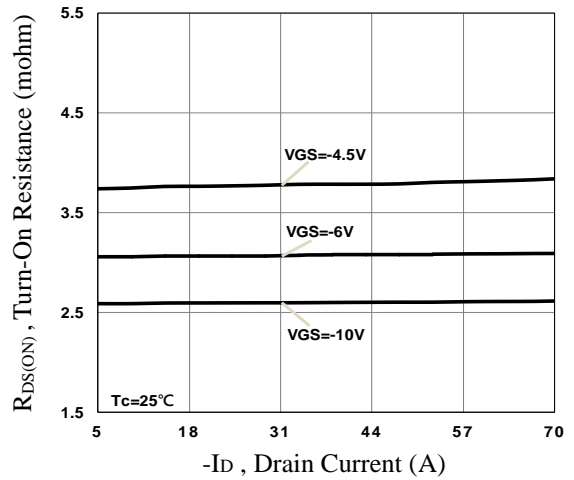
Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)

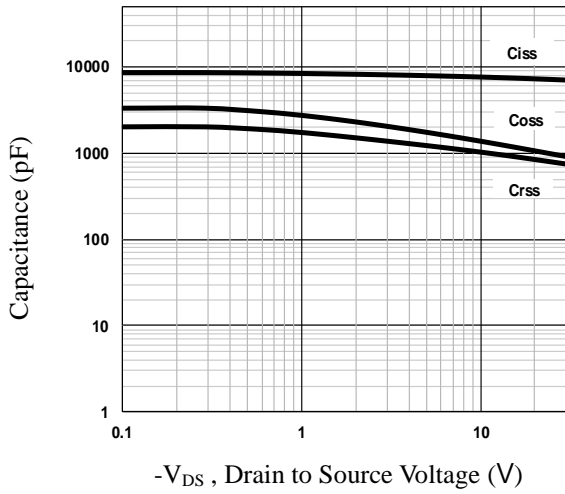
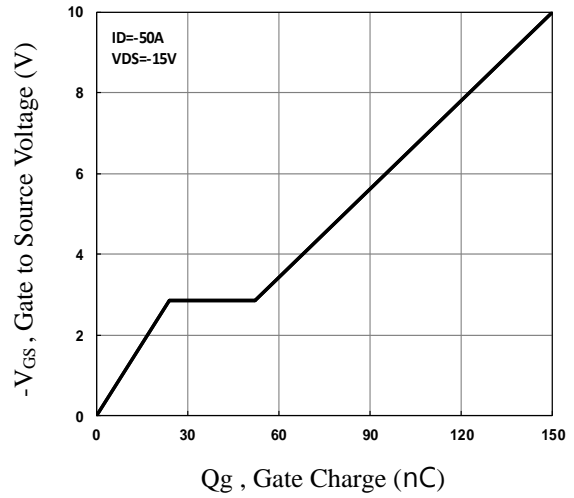
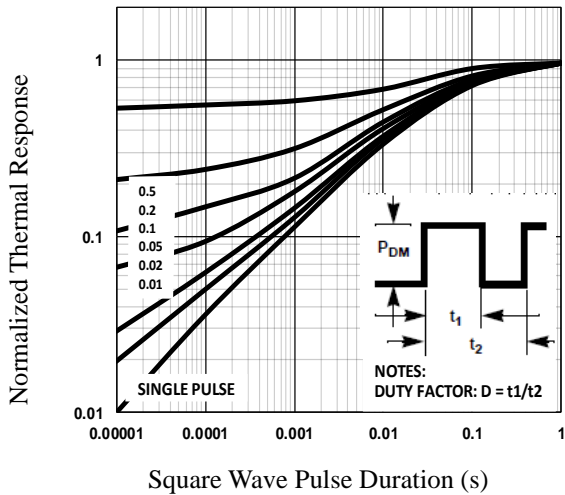
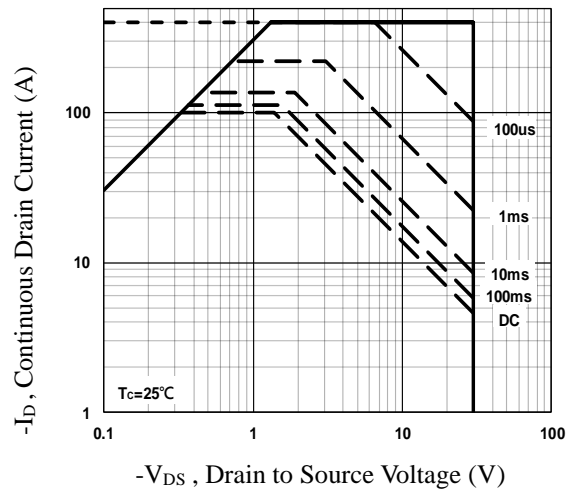
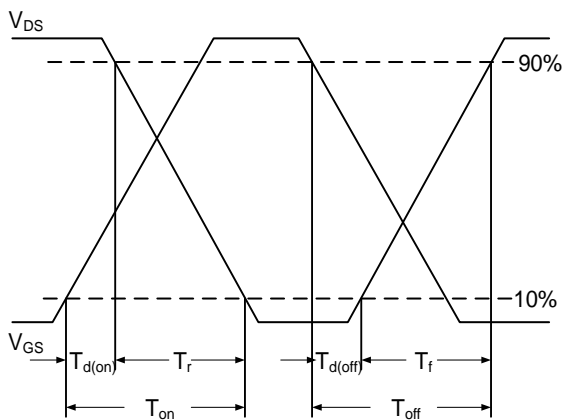
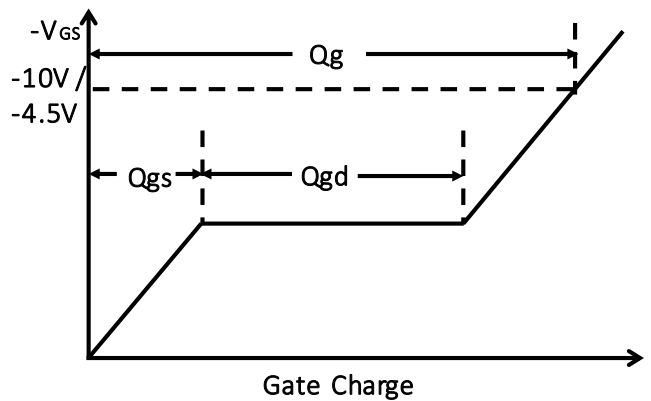
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=-250μA	-30	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=-30V,VGS=0V	--	--	-1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=-250μA	-1.2	-1.6	-2.3	V
gFS	Forward Transconductance	VDS=5V,ID=-20A	--	--	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=-10V, ID=-20A	--	2.9	3.9	mΩ
		VGS=-4.5V, ID=-10A	--	3.9	5.5	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=-15V,VGS=0V, F=1MHZ	--	5200	--	pF
Coss	Output Capacitance		--	1100	--	pF
Crss	Reverse Transfer Capacitance		--	920	--	pF
Rg	Gate resistance	f=1.0MHz	--	3.5	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=-10V,VDS=-15V, ID=-30A,RGEN=3Ω	--	25	--	nS
tr	Turn-on Rise Time		--	35	--	nS
td(off)	Turn-Off Delay Time		--	99	--	nS
tf	Turn-Off Fall Time		--	50	--	nS
Qg	Total Gate Charge	VGS=-10V, VDS=-15V, ID=-30A	--	150	--	nC
Qgs	Gate-Source Charge		--	24	--	nC
Qgd	Gate-Drain Charge		--	23	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	-138	A
VSD	Forward on Voltage	VGS=0V,IS=-20A	--	-0.8	-1.2	V
trr	Reverse Recovery Time	Isd=-30A , dI/dt=100A/μs , TJ=25°C	--	52	--	ns
Qrr	Reverse Recovery Charge		--	53	--	nc

Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

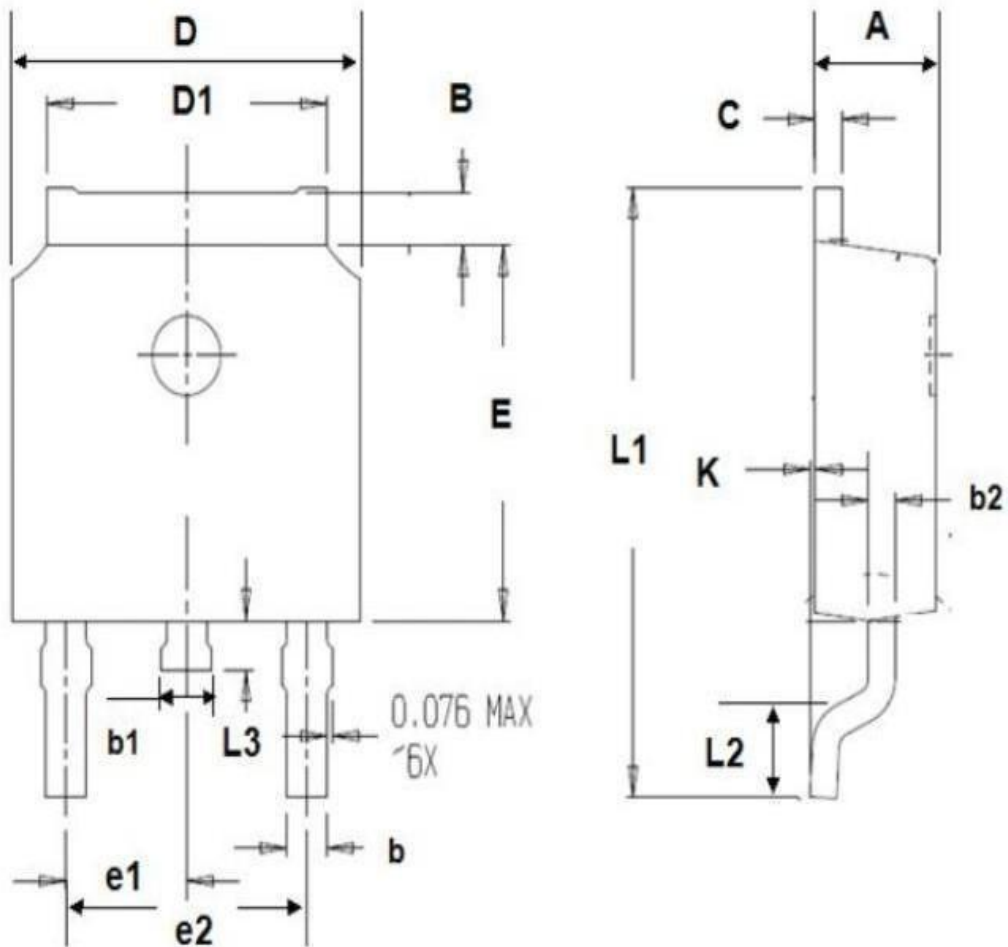
Notes 3.EAS condition: TJ=25°C


Fig.1 Typical Output Characteristics

Fig.2 Continuous Drain Current vs. T_C

Fig.3 Normalized $R_{DS(on)}$ vs. T_J

Fig.4 Normalized V_{th} vs. T_J

Fig.5 Turn-On Resistance vs. V_{GS}

Fig.6 Turn-On Resistance vs. I_D


Fig.7 Capacitance Characteristics

Fig.8 Gate Charge Characteristics

Fig.9 Normalized Transient Impedance

Fig.10 Maximum Safe Operation Area

Fig.11 Switching Time Waveform

Fig.12 Gate Charge Waveform

•Dimensions

SYMBOL	min	max	SYMBOL	min	max
A	2.10	2.50	B	0.85	1.25
b	0.50	0.80	b1	0.50	0.90
b2	0.45	0.70	C	0.45	0.70
D	6.30	6.75	D1	5.10	5.50
E	5.30	6.30	e1	2.25	2.35
L1	9.20	10.60	e2	4.45	4.75
L2	0.90	1.75	L3	0.60	1.10
K	0.00	0.23			




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